



---

**FINAL PRODUCT/PROCESS CHANGE NOTIFICATION #16876**

Generic Copy

---

**Issue Date:** 17-Jul-2012

**TITLE:** Transfer of HD1 MOSFETs from ON Semiconductor fab located in Aizu, Japan to ON Semiconductor Fab in Roznov, Czech Republic.

**PROPOSED FIRST SHIP DATE:** 17-Oct-2012

**AFFECTED CHANGE CATEGORY(S):** Wafer Fabrication

**AFFECTED PRODUCT DIVISION:** PowerFET Business Unit

**FOR ANY QUESTIONS CONCERNING THIS NOTIFICATION:**

Contact your local ON Semiconductor Sales Office or Larry DeLuca < [larry.deluca@onsemi.com](mailto:larry.deluca@onsemi.com) >

**SAMPLES:** Contact your local ON Semiconductor Sales Office or Brian Goodburn < [brian.goodburn@onsemi.com](mailto:brian.goodburn@onsemi.com) >

**ADDITIONAL RELIABILITY DATA:** Available

Contact your local ON Semiconductor Sales Office or Donna Scheuch < [d.scheuch@onsemi.com](mailto:d.scheuch@onsemi.com) >

**NOTIFICATION TYPE:**

Final Product/Process Change Notification (FPCN)

Final change notification sent to customers. FPCNs are issued at least 90 days prior to implementation of the change.

ON Semiconductor will consider this change approved unless specific conditions of acceptance are provided in writing within 30 days of receipt of this notice. To do so, contact <[quality@onsemi.com](mailto:quality@onsemi.com)>.

**DESCRIPTION AND PURPOSE:**

ON Semiconductor is notifying customers of its plan to transfer its High Cell Density HD1 MOSFETs from the ON Semiconductor fab located in Aizu, Japan to ON Semiconductor Fab in Roznov, Czech Republic. The Roznov facility currently produces a variety of products including High Cell Density MOSFETs (TMOS7 and HD+ technologies).

ON Semiconductor Roznov Wafer FAB is an internal factory that is ISO/TS 16949:2009, ISO 9001:2008, ISO 14000:2004 certified.

Reliability Qualification and full electrical characterization over temperature have been performed.



**FINAL PRODUCT/PROCESS CHANGE NOTIFICATION #16876**

**RELIABILITY DATA SUMMARY:**

Reliability Test Results	Test	Test Conditions	Read points	BSS84LT1G	MTB50P03HDLG	MGSF1N03LT1G	MMDF3N04
1	AC-PC	Ta = 121°C/ 100% RH/ 15psig	96hrs	0/154	0/77	0/77	0/77
2a	H3TRB-PC	85°C/85% RH for 1008 hr	1008 Hrs		0/77		
2b	HAST-PC	130°C/85% RH for 96 hrs	96hrs	0/154		0/77	0/77
3	HTGB	TA = Max rated for 1008 hrs 100% of Vgss Max	1008 Hrs	0/154	0/77	0/77	0/77
4	HTRB	TA = Max rated for 1008 hrs 80% of max rated Vdss	1008 Hrs	0/154	0/77	0/77	0/77
5	IOL	Ta=25°C, delta Tj=100°C, 2-min on/off, 15K- cy	15,000 Hrs	0/154	0/77	0/77	0/77
6	TC-PC	-55°C to +150°C for 1000 cycles	1000 cycles	0/154	0/77	0/77	0/77
7	SAT	Pre and Post MSL	1008 Hrs	0/10	0/10	0/10	0/10

**ELECTRICAL CHARACTERISTIC SUMMARY:**

There is no change in electrical parametric performance. Characterization data is available upon request.

**CHANGED PART IDENTIFICATION:**

There will be no physical change to the Devices assembled with ON Semiconductor Die from either wafer facility in Aizu, Japan or Roznov, CR. There will be Wafer Lot traceability from the manufacturing Lot to determine the Die origin. Product assembled with the Die potentially fabricated from the Roznov wafer facility will have a Finish Good Date Code of work week 42, 2012 and newer indicating the Die could come from either Aizu or Roznov.

**List of affected General Parts:**

BSS84LT1G	MMBF0201NLT1G	MVGSF1N03LT1G
BSS84LT1H	MMBF2201NT1G	MVMBF0201NLT1G
BVSS84LT1G	MMSF3P02HDR2G	MVMBF0201NLT1G
MGSF1N02LT1G	MTB50P03HDLT4G	MVSF2N02ELT1G
MGSF1N03LT1G	MTP50P03HDLG	NVF2201NT1G
MGSF2N02ELT1G	MVDF2C03HDR2G	SBSS84LT1G